

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

SANG-HYUN OH, ET AL.

Application No.:

Filed:

For: **METHOD FOR MANUFACTURING
FERROELECTRIC RANDOM ACCESS
MEMORY CAPACITOR**

Art Group:

Examiner:

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

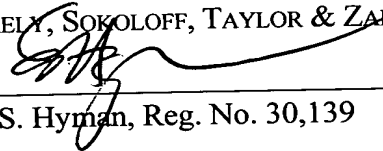
In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP



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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

C mplete if Known

Application Number

Filing Date

First Named Inventor

Sang-Hyun Oh

Art Unit

Examiner Name

Attorney Docket Number

51876P413

Sheet

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Examiner Signature		Date Considered	
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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Based on PTO/SB/08A (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wtr) 08/11/2003.

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Information Disclosure Statement

New U.S. Patent Application for
METHOD FOR MANUFACTURING
FERROELECTRIC RANDOM ACCESS MEMORY CAPACITOR
Our Ref. No.: P03H8025/US/gy

Reference No.:

- (1) US Patent No. 6,573,553
- (2) US Patent No. 6,548,343
- (3) US Patent No. 6,576,546
- (4) US Patent No. 6,573,587
- (5) US Patent No. 6,407,422
- (6) US Patent No. 6,596,547